

CMPT3019 (3DG3019)

硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:用于一般普通放大。

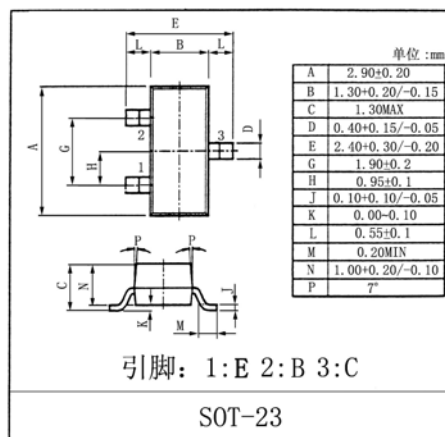
Purpose: General purpose amplifier applications

特点: 大电流。

Features: High current.

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	120	V
V _{CE0}	80	V
V _{EB0}	7.0	V
I _C	500	mA
I _{CM}	1.0	A
P _C	350	mW
T _j	150	°C
T _{stg}	-55~150	°C



电性能参数/Electrical characteristics(Ta=25°C)

参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =100 μ A	I _E =0	120			V
V _{CE0}	I _C =30mA	I _B =0	80			V
V _{EB0}	I _E =100 μ A	I _C =0	7.0			V
I _{CB0}	V _{CB} =90V	I _E =0			0.01	μ A
I _{EB0}	V _{EB} =5.0V	I _C =0			0.01	μ A
h _{FE(1)}	V _{CE} =10V	I _C =150mA	100		300	
h _{FE(2)}	V _{CE} =10V	I _C =500mA	50			
h _{FE(3)}	V _{CE} =10V	I _C =10mA	90			
h _{FE(4)}	V _{CE} =10V	I _C =0.1mA	50			
V _{CE(sat)(1)}	I _C =150mA	I _B =15mA			0.2	V
V _{CE(sat)(2)}	I _C =500mA	I _B =50mA			0.5	V
V _{BE(sat)}	I _C =150mA	I _B =15mA			1.1	V
f _T	V _{CE} =10V I _C =50mA	f=1.0MHz	100			MHz
C _{ob}	V _{CB} =10V I _E =0	f=1.0MHz			12	pF
C _{ib}	V _{EB} =0.5V I _C =0,	f=1.0MHz			60	pF
NF	V _{CB} =10V R _S =1K Ω	I _C =100mA f=1.0KHz			4.0	dB

印章/Marking: HC3A